AMENDMENTS TO THE SPECIFICATION

Please delete paragraph [01] and replace it with the following replacement paragraph marked up to show changes made relative to the immediate prior version:

[01] ~~[Not Applicable]~~ The present application is a continuation of U.S. Application Serial No. 10/038,021 filed January 3, 2002 which is incorporated herein by reference in its entirety.

Please delete paragraph [10] and replace it with the following replacement paragraph marked up to show changes made relative to the immediate prior version::

[10] The dielectric material separating the polysilicon gate from the channel region usually consists of thermally grown oxide material, silicon dioxide (SiO_2) for example, where the oxide is about 2.5nm thick or less. Here the thin oxide leaks very little current, through a mechanism called Fowler-Nordheim tunneling, under voltage stress. When this thin gate-ox transistor or fuse is stressed beyond a critical electrical field (applied voltage divided by the thickness of the oxide) the oxide ruptures, destroying (alternatively referred to as "blowing") the transistor or fuse. If the fuse is connected or coupled to a storage element as part of a memory cell as disclosed in commonly assigned application Serial No. ~~_____~~ 10/025,132 (Attorney Ref. No. 13374US01), titled "Memory Cell with Fuse Element", now U.S. Patent No. 6,525,955 issued February 25, 2003, the complete subject matter of which is incorporated herein by reference, blowing the transistor or fuse sets the state or programs the storage element and thus the memory cell.